

Photodetector Performance of Iron – doped MoS₂ - Based Field Effect Transistor Devices



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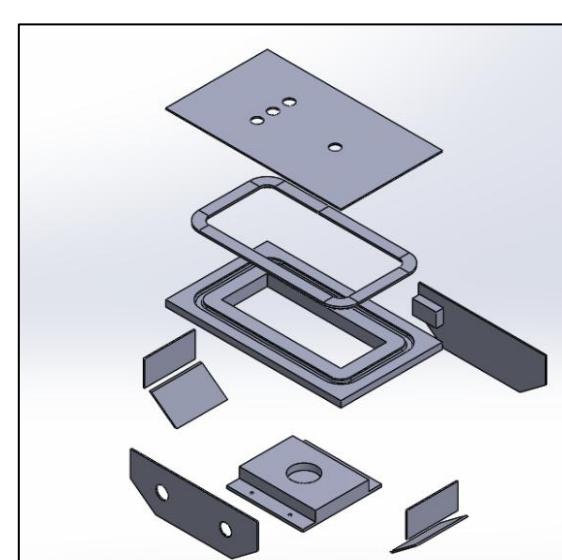
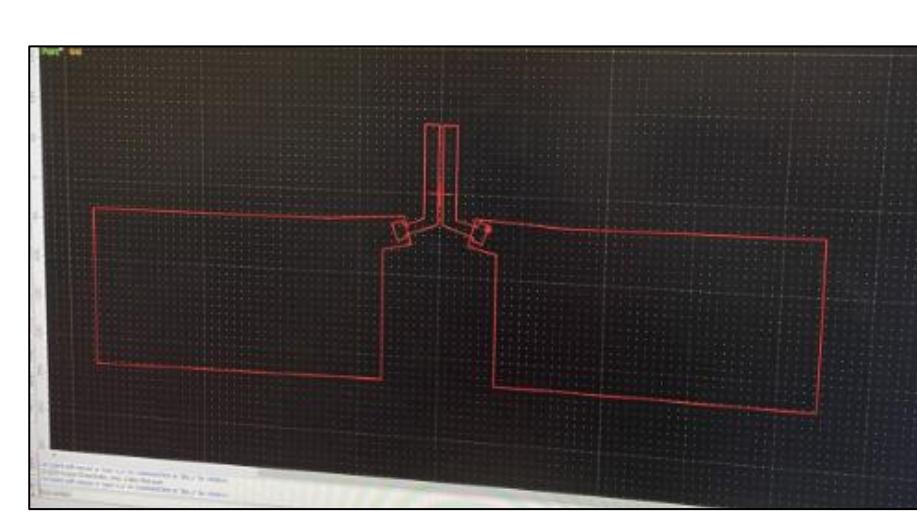
Introduction

Burning fossil fuels release carcinogens such as nitrogen dioxide and sulfur dioxide. The US EPA has limited exposure of these gases to 53 ppb and 75 ppb, respectively. Due to this, a gas sensor that can detect in ppb levels is necessary to ensure the air we breathe is safe. Molybdenum disulfide is a two-dimensional transition metal dichalcogenide (TMD). Monolayer, single crystal Fe/MoS₂ form direct bandgap semiconductors that have applications in FET devices that can be used as ppb gas sensors.

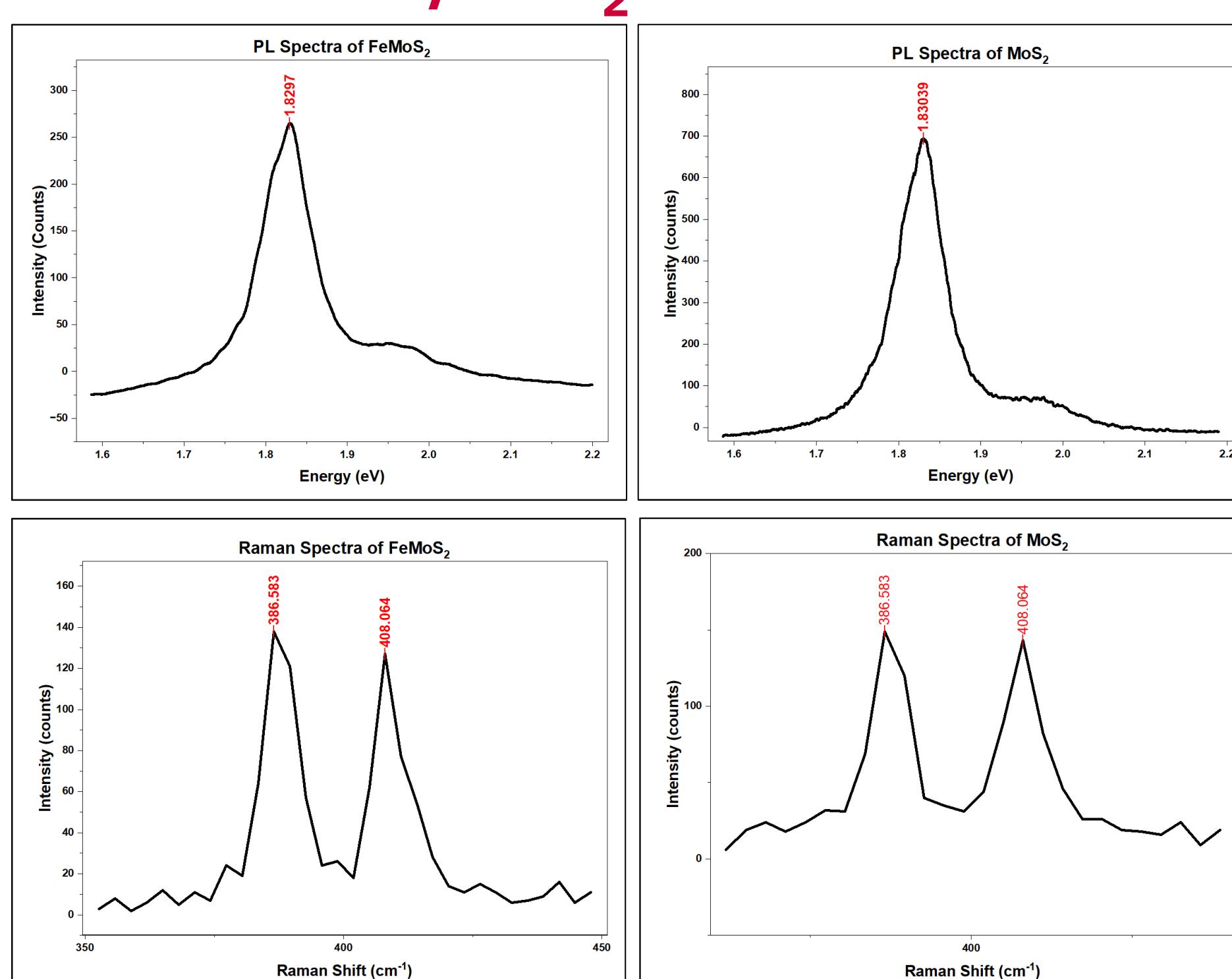
Methodology

Procedures:

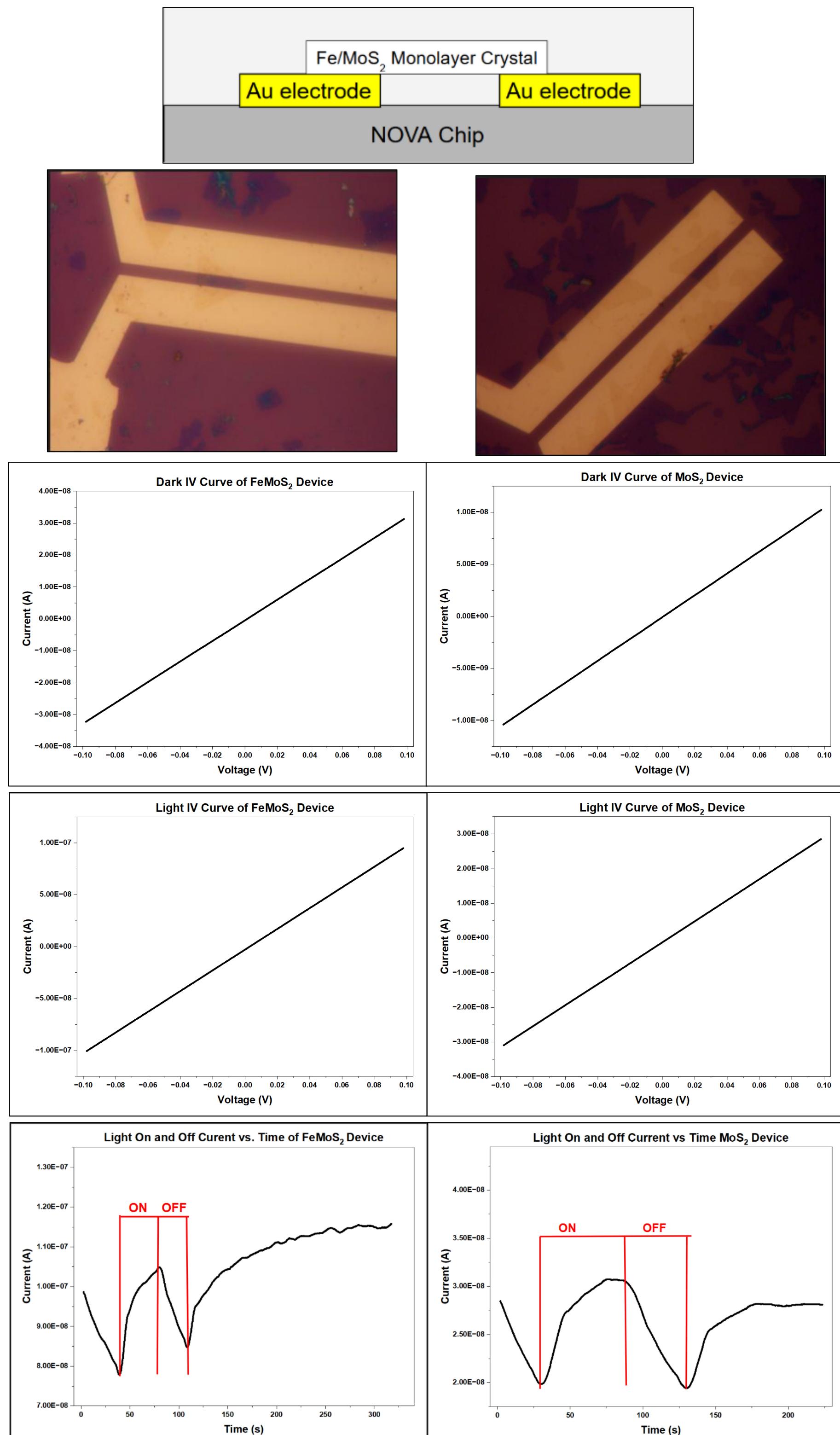
- **Contact Chemical Vapor Deposition Growth Process:** Used to grow Fe MoS₂ and MoS₂.
- **Electron Beam Lithography Metal Deposition:** Electrode pattern is etched onto PMMA coated NOVA silicon chips and gold is deposited to create the gold electrodes.
- **PMMA Wet Transfer Process:** Used to fabricate FET devices by joining crystals and gold electrodes.
- **IV Measurements:** Used to characterize fabricated Fe/ MoS₂ FET devices.
- **Gas Sensing Chamber Design:** Used to perform gas sensing tests on fabricated Fe/ MoS₂ FET devices.



Results – Fe/MoS₂ Characterization



Results - Fe/MoS₂ FET IV Characterization



Discussion

This project provides a comprehensive IV characterization of Fe/MoS₂ FET devices. Key findings include dark IV measurements, light IV measurements, and light on and off current measurements with a light power 15.844 nW. The FeMoS₂ FET devices have an overall lower resistance and higher increase in current during the light on and off current test.

Limitations: The project's limitations include the absence of different tubes used in the contact CVD growth process. As well, budget constraints to fabricate a gas sensing apparatus for gas sensing tests.

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